

20th Anniversary

IMFEDK2022

The 2022 International Meeting for
Future of Electron Devices, Kansai

Photo Album

November 28-30, 2022
Kyoto Avanti Hall & Zoom Online

Opening Remarks 11/28



IEEE Online & Onsite : Avanti Kyoto Hall, Kyoto, 28th-30th Nov., 2022

IMFEDK The 2022 International Meeting for Future of Electron Devices, Kansai

IMFEDK has been giving scientists chances to disseminate their research results and university students opportunity to grow on their own.

TECHNICAL SPONSOR & FINANCIAL SPONSOR

- IEEE EDS Kansai Chapter
- IEEE LEON LAVES DCTV
- The Technical Committee on Electron Devices, Silicon Devices and Materials, IIC
- IEEE SMCs Kansai Chapter
- Endorsed by The Japan Society of Applied Physics
- IEEE CS Kansai Chapter
- IEEE COMPUTER SOCIETY



Keynote Speech 1

Multiple Design Options for SOEN

- Collaborators had multiple design decisions for designing SOEN, including different neuron model implementations
- The key question is which model performs best when implemented on a particular application

SOEN1

SOEN2

Wardley, Sonia, Adam N. McGeagh, Jeff Chies, Richard P. Minn, Seo Woo Nam, Jeffrey M. Shainline, Grant Bruce, James S. Paris, and Catherine D. Stevens. "Design of superconducting nanoelectronic networks for neuromorphic computing." In 2019 IEEE International Conference on Reconfigurable Computing (ICRC), pp. 1-7. IEEE, 2019.

THE UNIVERSITY OF TENNESSEE KNOXVILLE



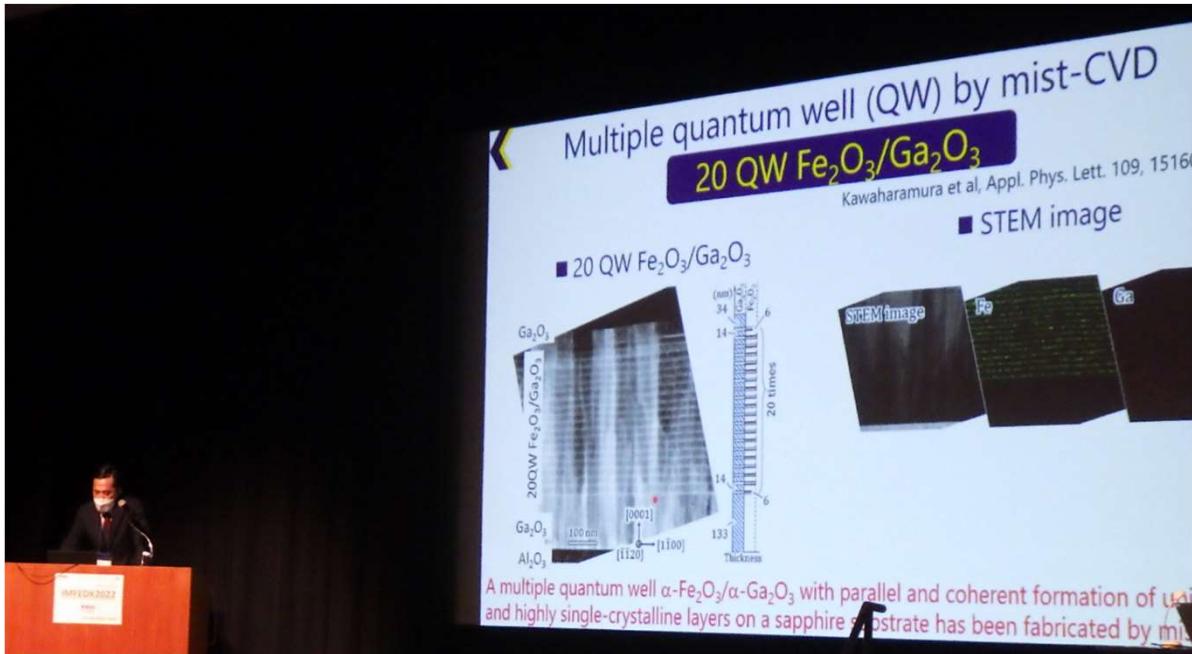
General Session –Emerging 1-



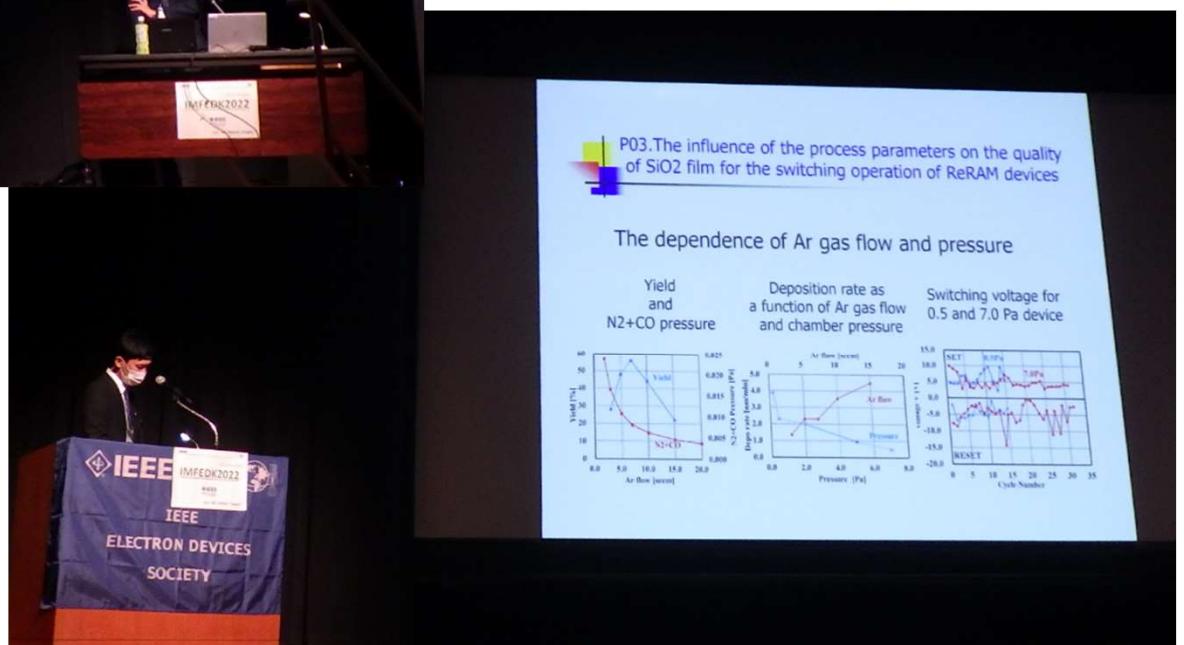
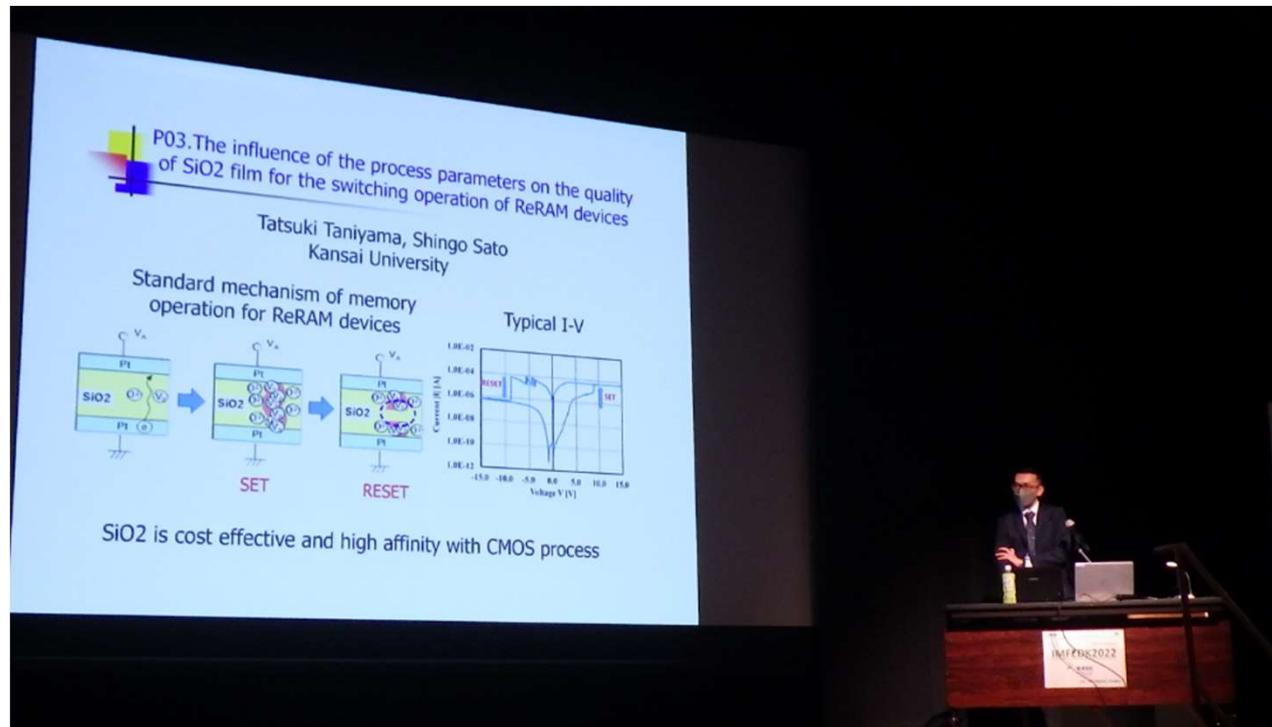
General Session –Compound 1-



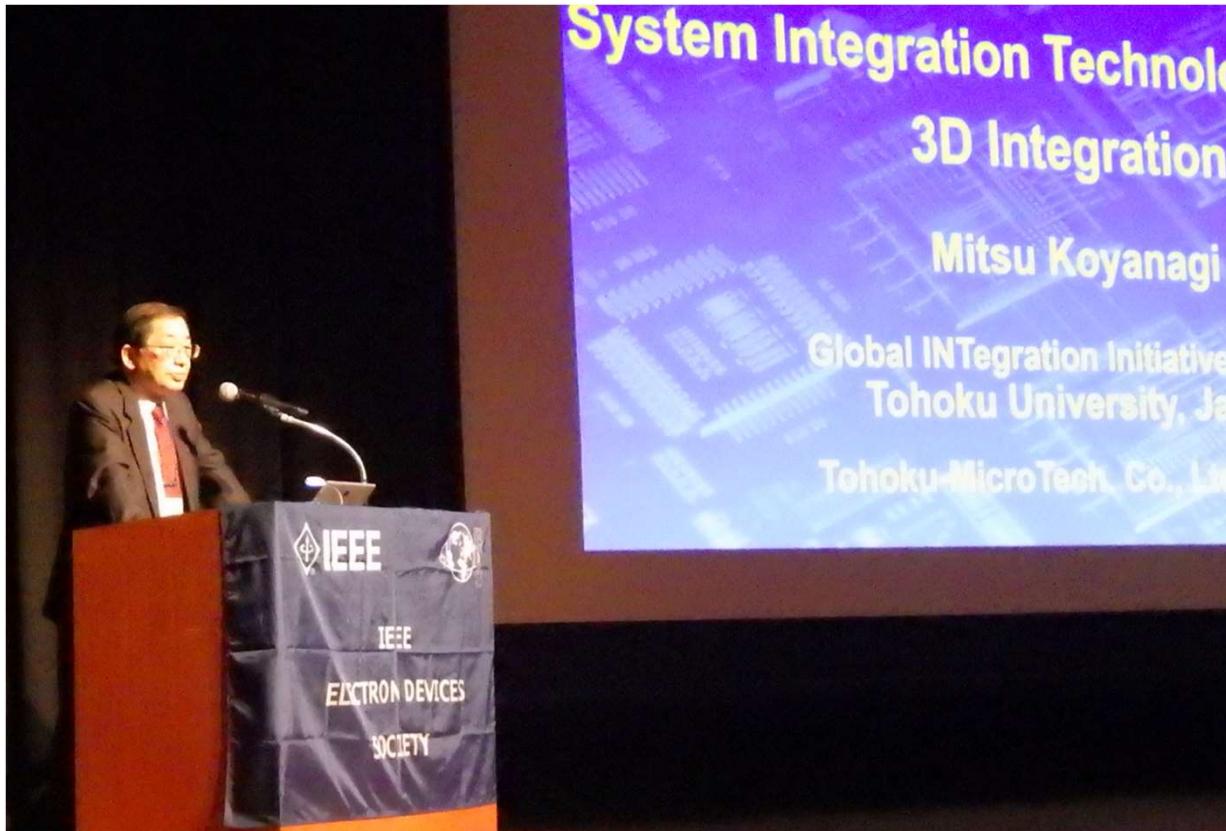
General Session - Compound 2 -



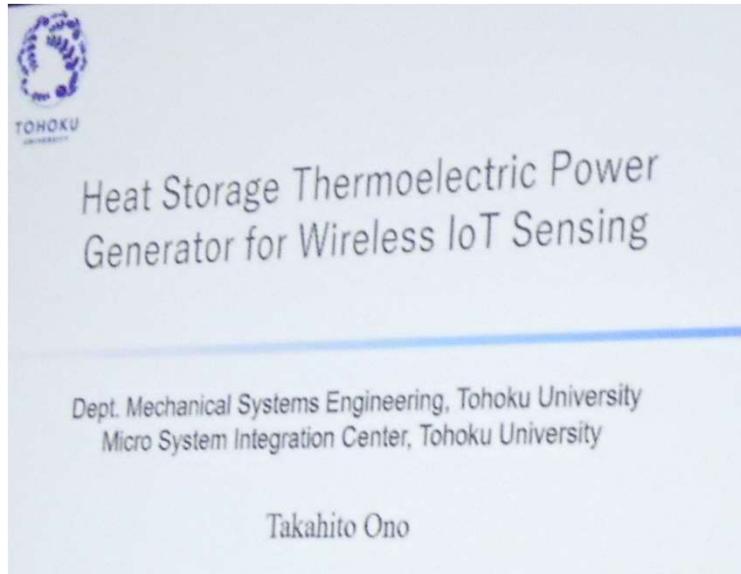
Poster Oral Short Presentation 11/29



Keynote Speech 2



General Session - Emerging 2 -

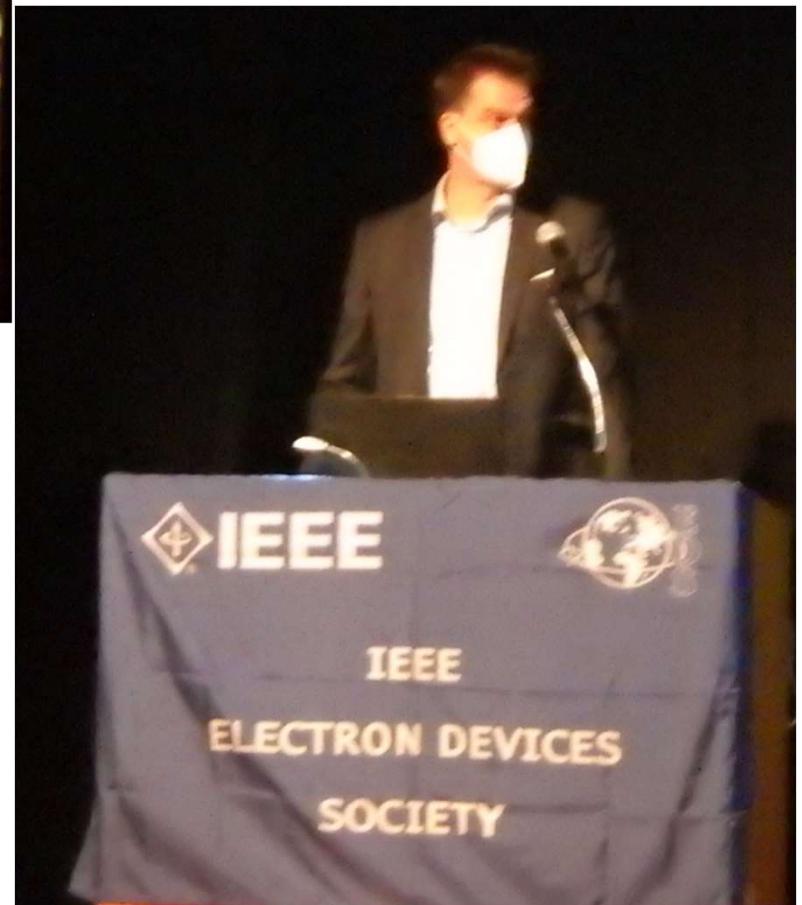


TOHOKU UNIVERSITY

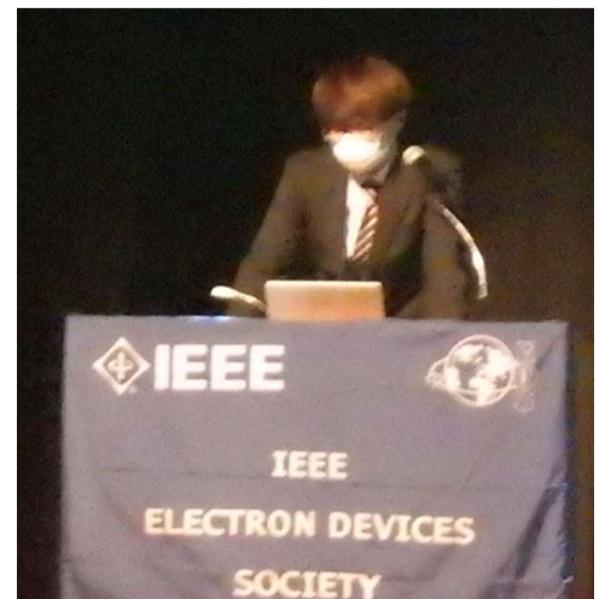
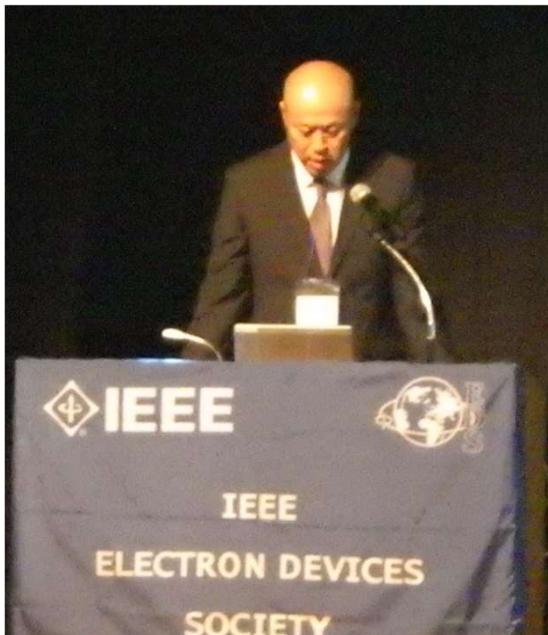
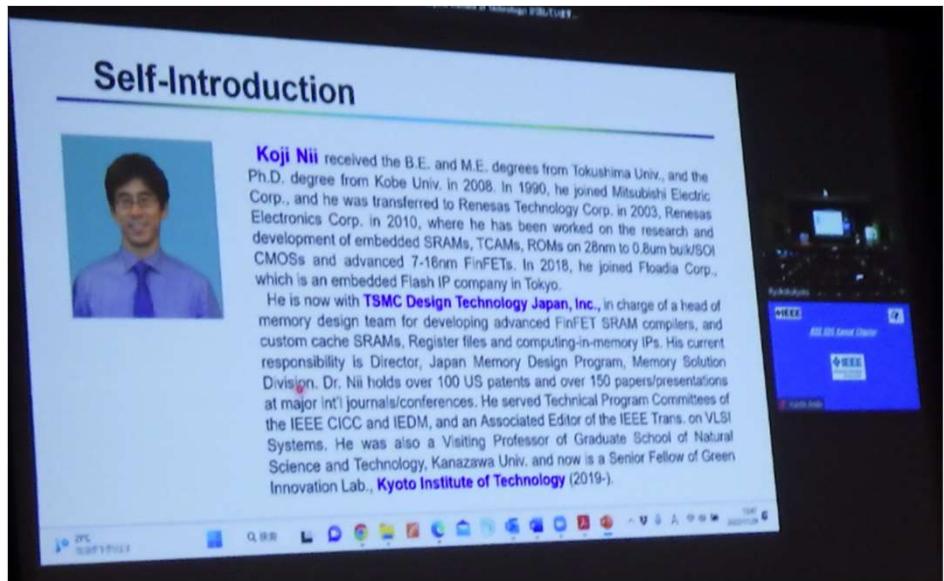
Heat Storage Thermoelectric Power Generator for Wireless IoT Sensing

Dept. Mechanical Systems Engineering, Tohoku University
Micro System Integration Center, Tohoku University

Takahito Ono



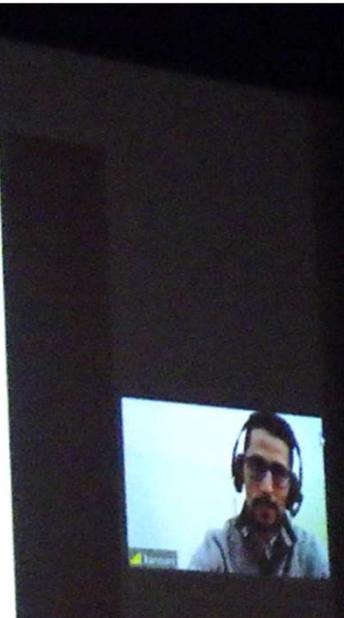
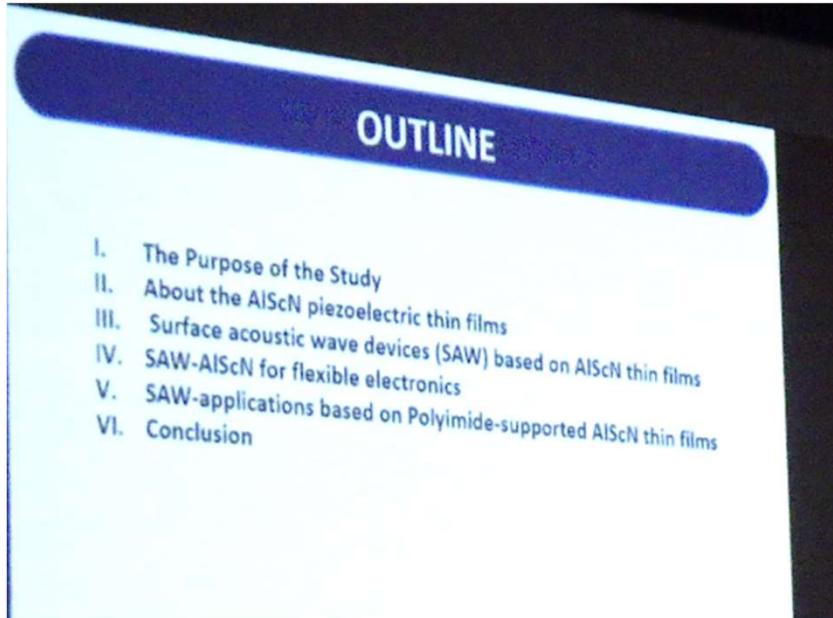
Special Session – Supported by IEEE SSCS Kansai Chapter -



General Session - Silicon 1 -



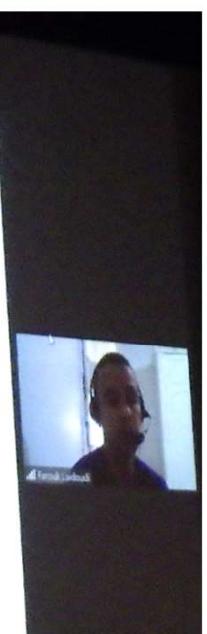
General Session - Emerging 3 -



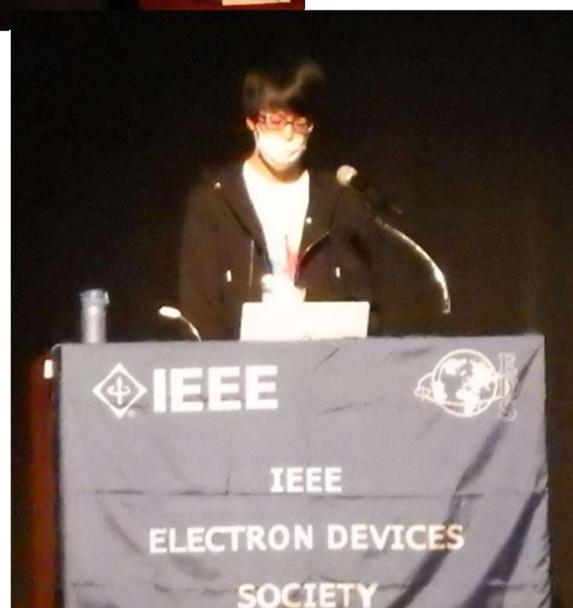
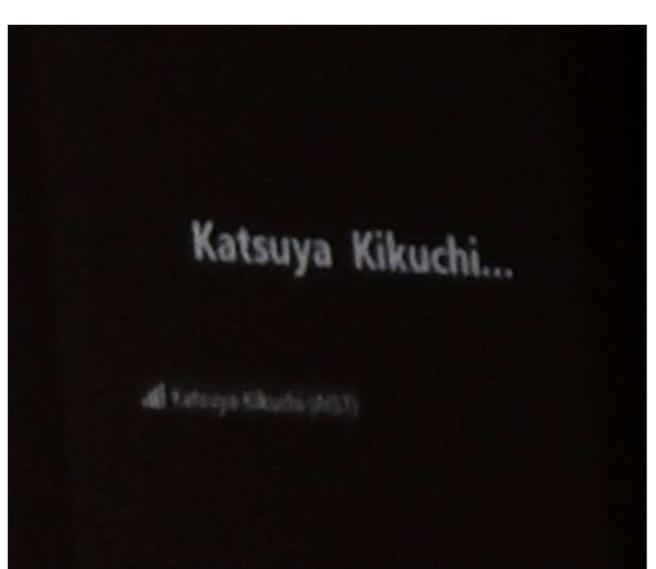
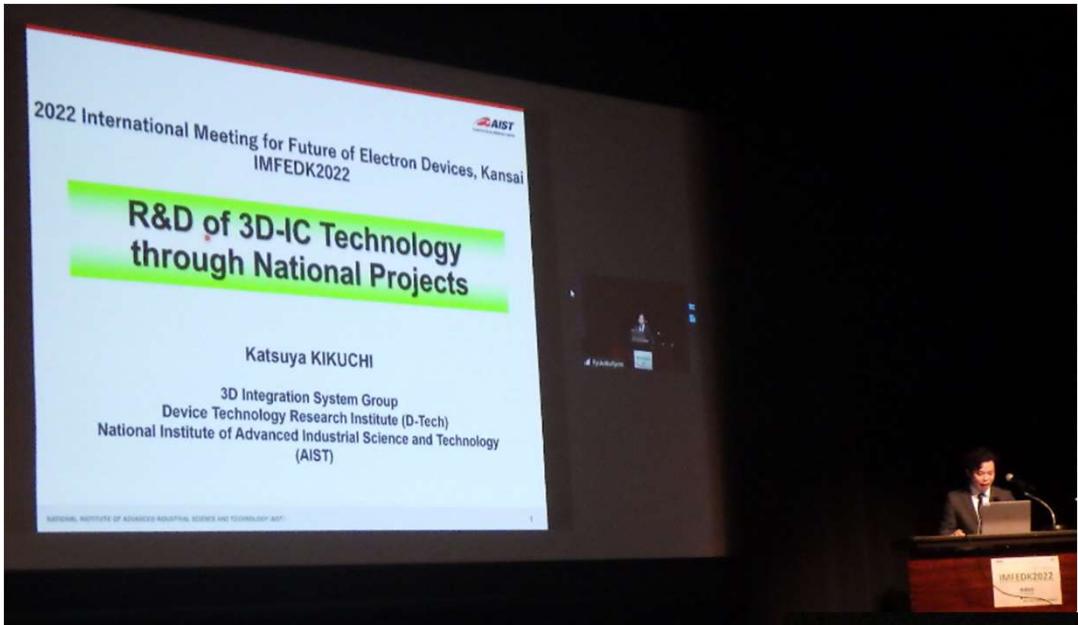
problem



- ❑ Characterizing liquids is of a major interest in different industrial applications: Oil, Biology and Medicine
- ❑ Developing high sensitivity sensors depends upon the used technic, the kind of the device, the constructive material
- ❑ Acoustic piezoelectric sensors, could be the key toward the development of safe, precise and high sensitive sensors for liquid environments
- ❑ Many approaches have been adopted to increase sensitivity of acoustic sensors: by doping the piezoelectric crystal, tilting it or exploiting new cuts and acoustic modes (Symmetric Lamb, SH-SAW, PSAW)
- ❑ Modifying the propagation path could be an issue for developing new Kind of high sensitive acoustic devices operating in liquid environment.
- ❑ Study the sensitivity to liquid characteristics of the higher order symmetric Lamb mode S2, in LiNbO₃ single plate with grooved micro-channels in the propagation path.



General Session - Silicon 2 - 11/30



Special Session

– IMFEDK Celebrating the 20th Anniversary –



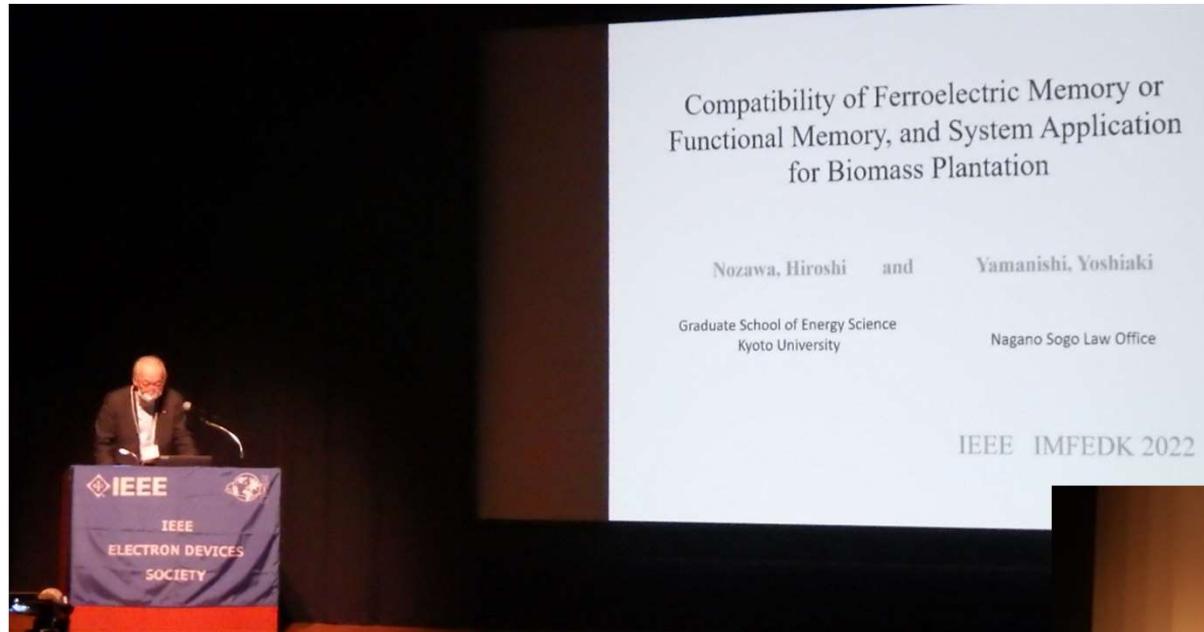
IEEE EDS Kansai Chapter Distinguished Service Award

Hiroshi Nozawa
(Kyoto University)

Daisuke Ueda
(Nagoya University)

Kenji Taniguchi
(Osaka University)



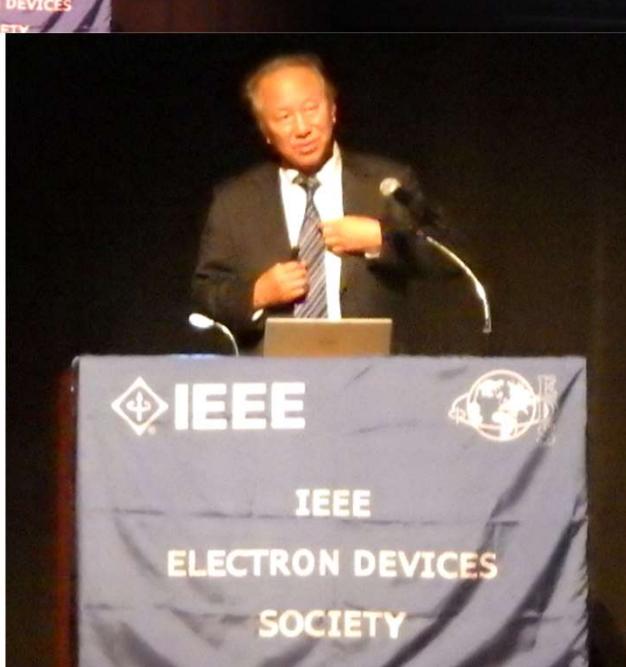


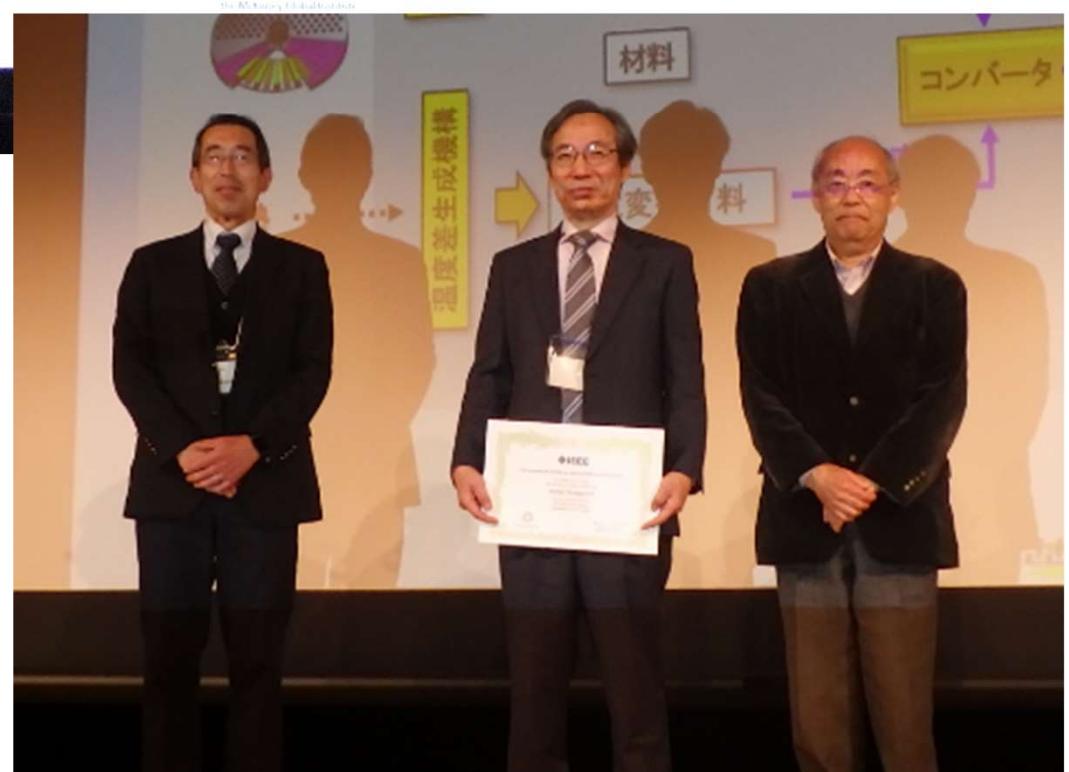
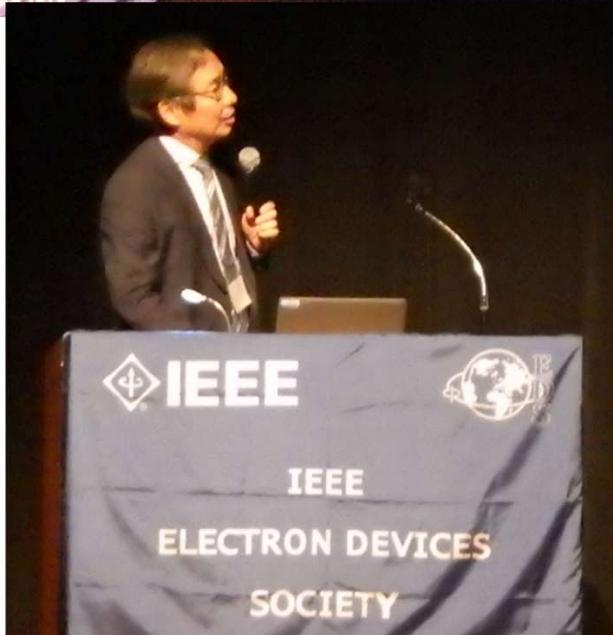
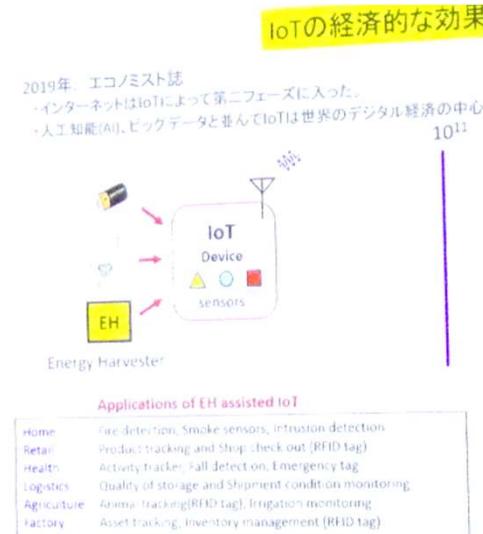


日本の半導体産業は衰退しているか？

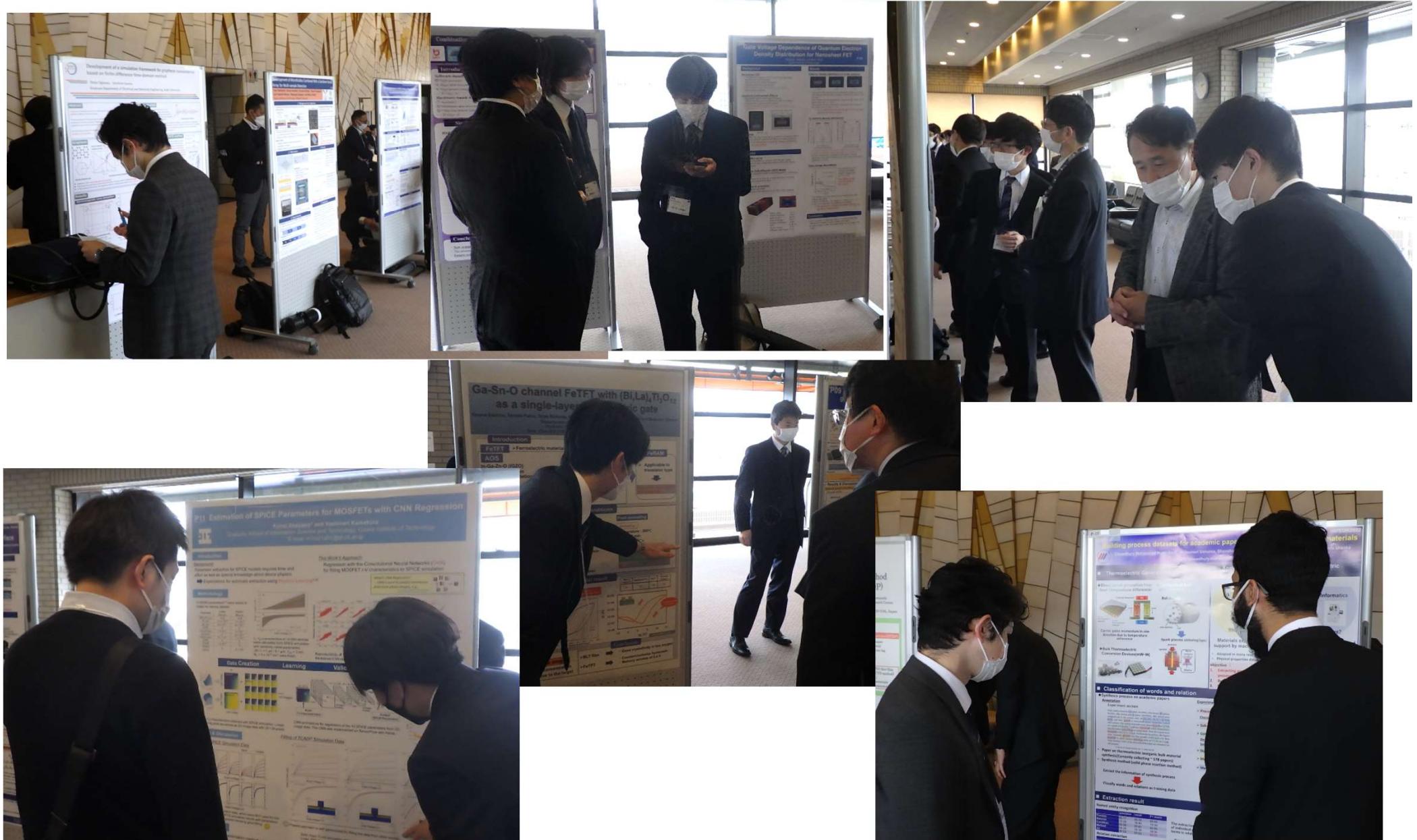
概要

1. 技術者としての昔話
2. 垂直統合と水平分業の利害得失
3. 海外との競争条件はどこが違うか？
4. 経営品質、3σ、ISOなどの技術管理は何だったか？
5. 技術的挑戦からの事業化が難しい組織環境
6. 皆さんの技術を事業化してみませんか
7. 展開シナリオを思い描ける技術者像

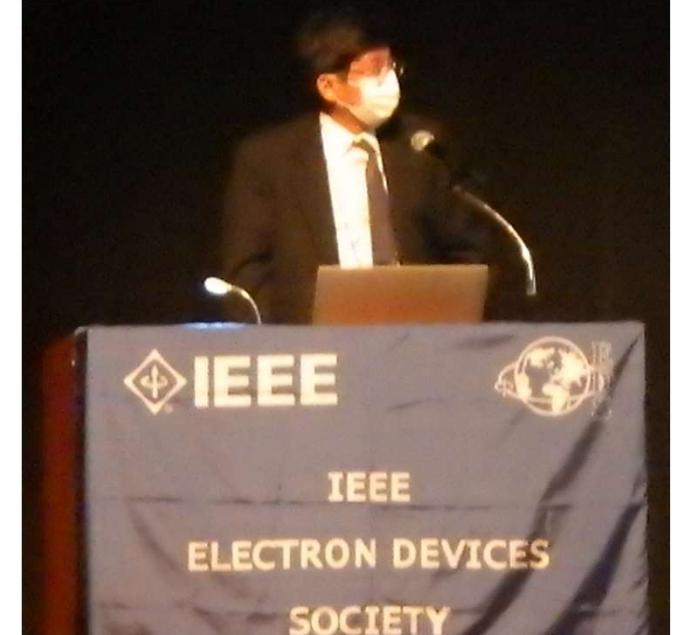




Poster Viewing and Discussion



INDUSTRIAL SESSION





IEEE EDS Kansai Chapter IMFEDK Most Downloaded Paper Award

**“An 800-MHz 8-bit High Speed SAR ADC
in 16nm FinFET Process”**

Keisuke Okuno, Koji Obata, Takumi Kato and Koji Sushihara

**“Development of SiC Power Devices and Modules
for Automotive Motor Drive Use”**

Tristan Evans, Toshio Hanada, Yuki Nakano and Takashi Nakamura

**“Improvement of Drain Leakage Current Characteristics
in Metal-Oxide-Semiconductor-Field-Effect-Transistor
by Asymmetric Source-Drain Structure”**

Byoungseon Choi, Hyunae Park, Dongsoo Kim and Byoungdeog Choi

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IEEE EDS Kansai Chapter IMFEDK Poster Paper Award



P11 “Estimation of SPICE Parameters for MOSFETs
with CNN Regression”

Kohei Akazawa
(Osaka Institute of Technology)



P04 “The Impact of Carrier Lifetime on the Electrical
Characteristics of Z2-FET”

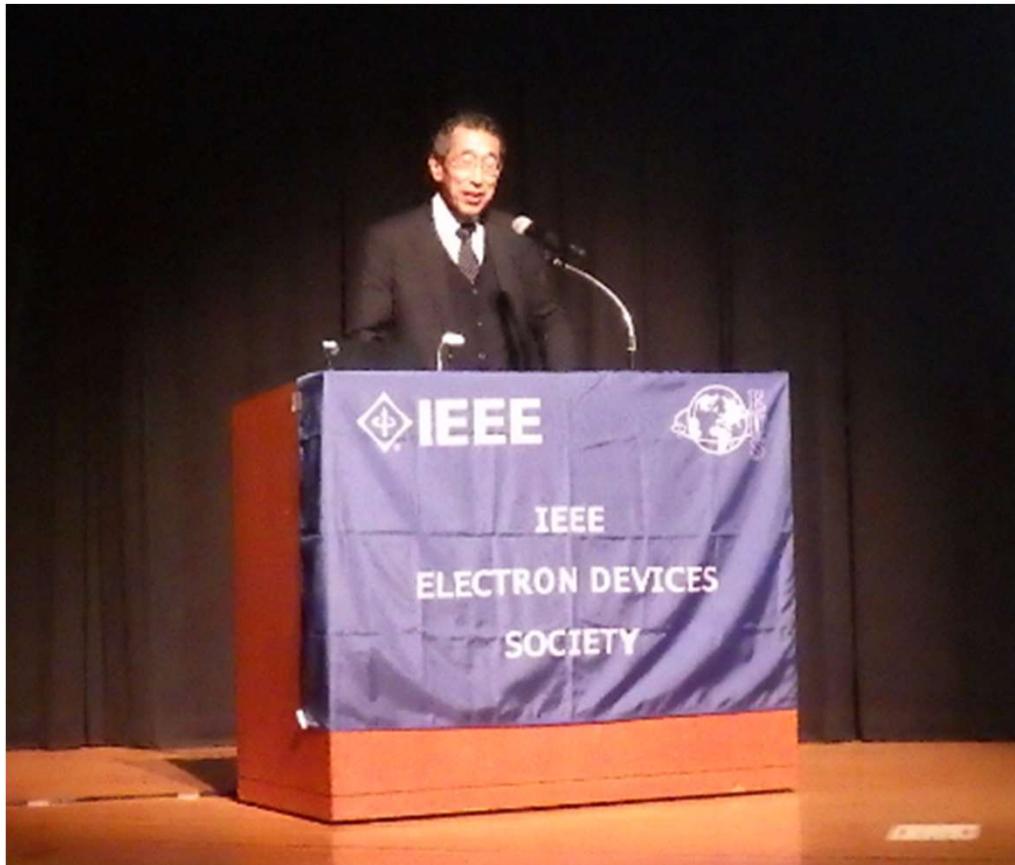




IEEE EDS Kansai Chapter IMFEDK Best Paper Award



Closing Remark



Edited by Yuichi Ando